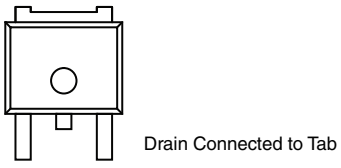
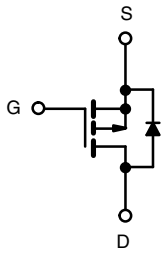
Automotive P-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 80
$R_{DS(on)}$ (Ω) at V_{GS} = - 10 V	0.028
I_D (A)	- 48
Configuration	Single

TO-252



Top View



P-Channel MOSFET

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified[d]
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

AUTOMOTIVE GRADE

RoHS COMPLIANT

HALOGEN FREE

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P08-28-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	- 80	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C	I_D	- 48	A
	T_C = 125 °C		- 28	
Continuous Source Current (Diode Conduction)[a]		I_S	- 50	
Pulsed Drain Current[b]		I_{DM}	- 190	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	- 45	
Single Pulse Avalanche Energy		E_{AS}	100	mJ
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	136	W
	T_C = 125 °C		45	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR-4 material).
d. Parametric verification ongoing.

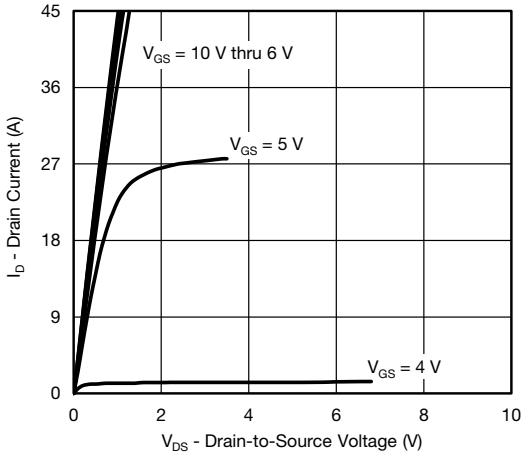
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = - 250 µA		- 80	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA		- 2.5	- 3.0	- 3.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = - 80 V	-	-	- 1	µA
		V_{GS} = 0 V	V_{DS} = - 80 V, T_J = 125 °C	-	-	- 50	
		V_{GS} = 0 V	V_{DS} = - 80 V, T_J = 175 °C	-	-	- 250	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = - 10 V	$V_{DS} \leq$ - 5 V	- 50	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V	I_D = - 12.5 A	-	0.023	0.028	Ω
		V_{GS} = - 10 V	I_D = - 12.5 A, T_J = 125 °C	-	-	0.049	
		V_{GS} = - 10 V	I_D = - 12.5 A, T_J = 175 °C	-	-	0.061	
Forward Transconductance[b]	g_{fs}	V_{DS} = - 15 V, I_D = - 12.5 A		-	32	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = - 25 V, f = 1 MHz	-	4826	6035	pF
Output Capacitance	C_{oss}			-	343	430	
Reverse Transfer Capacitance	C_{rss}			-	224	280	
Total Gate Charge[c]	Q_g	V_{GS} = - 10 V	V_{DS} = - 40 V, I_D = - 12.5 A	-	95	145	nC
Gate-Source Charge[c]	Q_{gs}			-	19	-	
Gate-Drain Charge[c]	Q_{gd}			-	26	-	
Gate Resistance	R_g	f = 1 MHz		1.73	3.47	5.21	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 40 V, R_L = 3.8 Ω $I_D \cong$ - 10.5 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	15	23	ns
Rise Time[c]	t_r			-	11	17	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	65	98	
Fall Time[c]	t_f			-	16	24	
Source-Drain Diode Ratings and Characteristics[b]							
Pulsed Current[a]	I_{SM}			-	-	- 190	A
Forward Voltage	V_{SD}	I_F = - 10 A, V_{GS} = 0		-	- 0.82	- 1.5	V

Notes

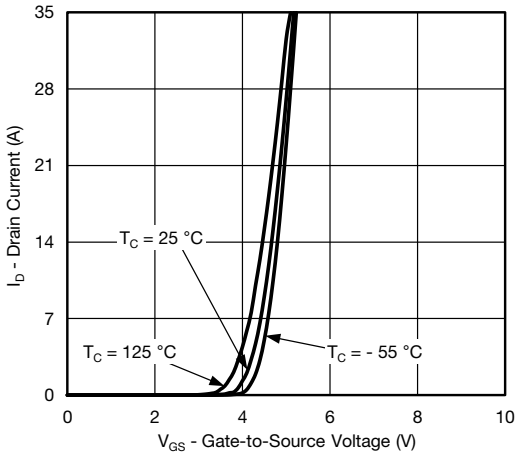
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

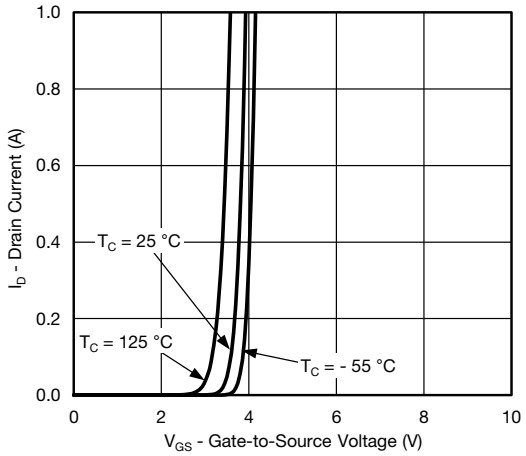
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



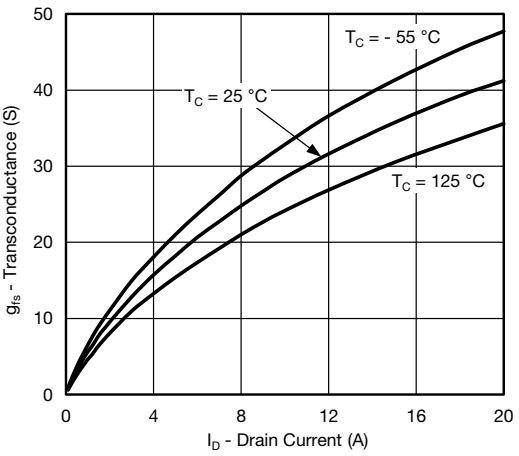
Output Characteristics



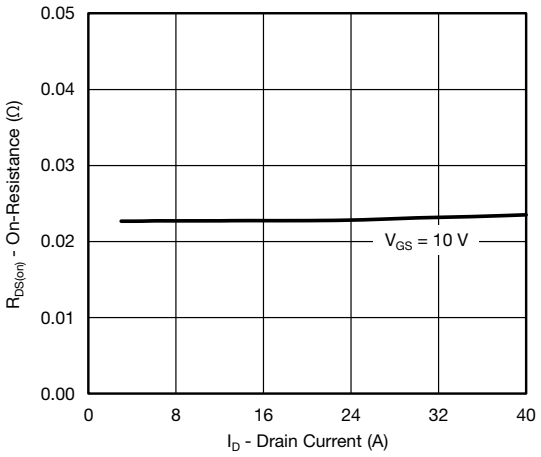
Transfer Characteristics



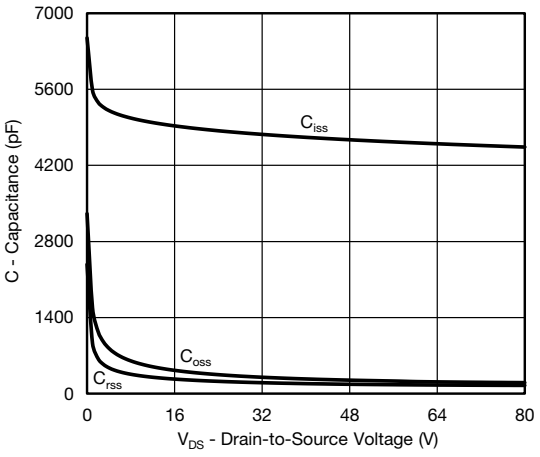
Transfer Characteristics



Transconductance

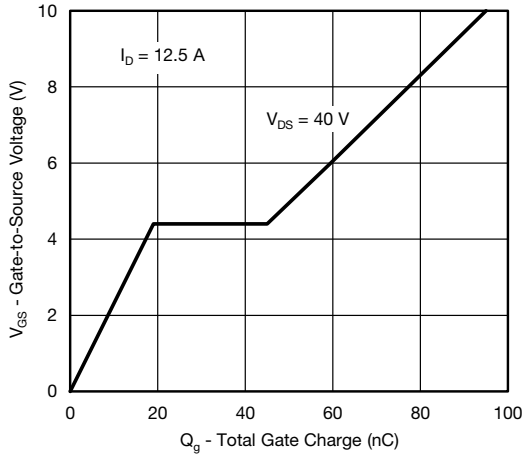


On-Resistance vs. Drain Current

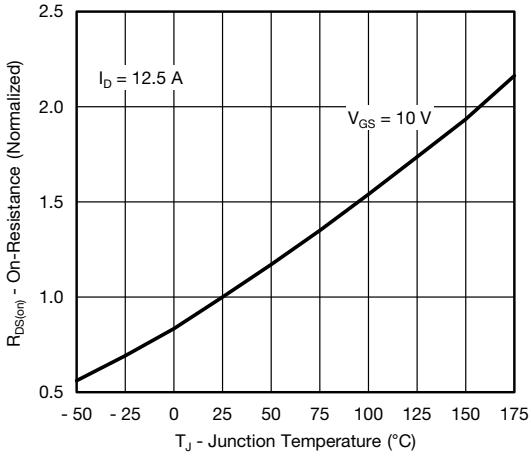


Capacitance

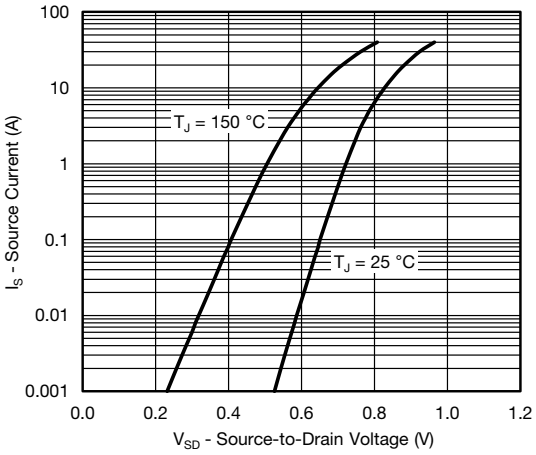
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



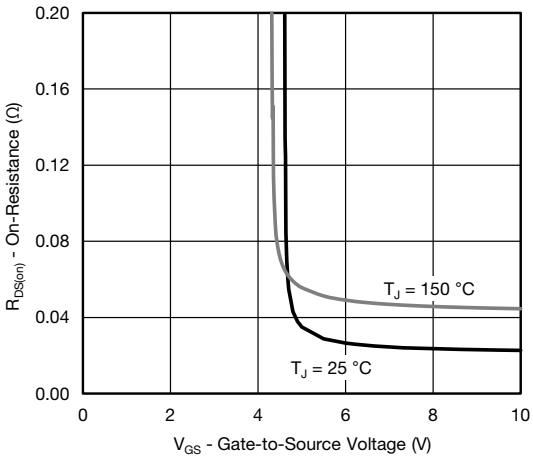
Gate Charge



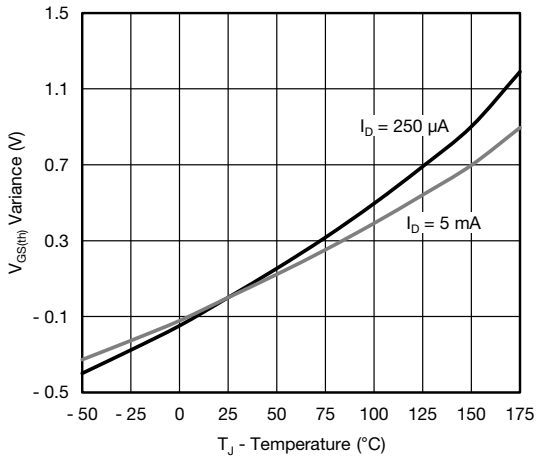
On-Resistance vs. Junction Temperature



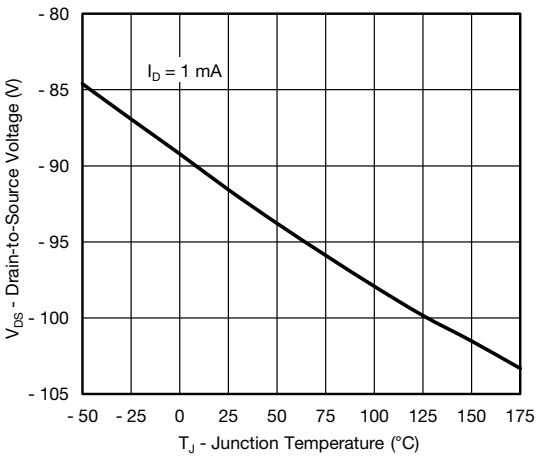
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

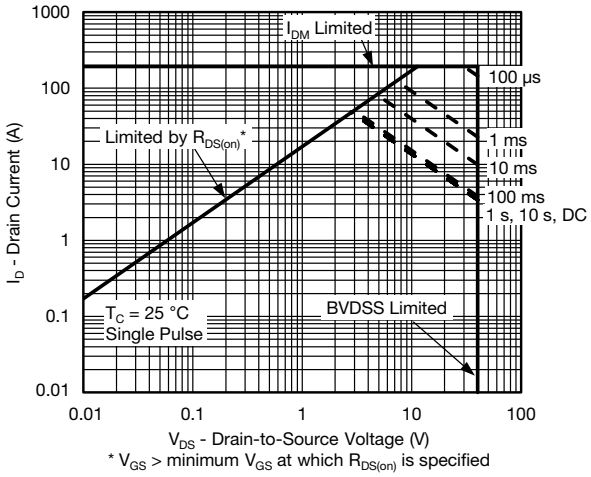


Threshold Voltage

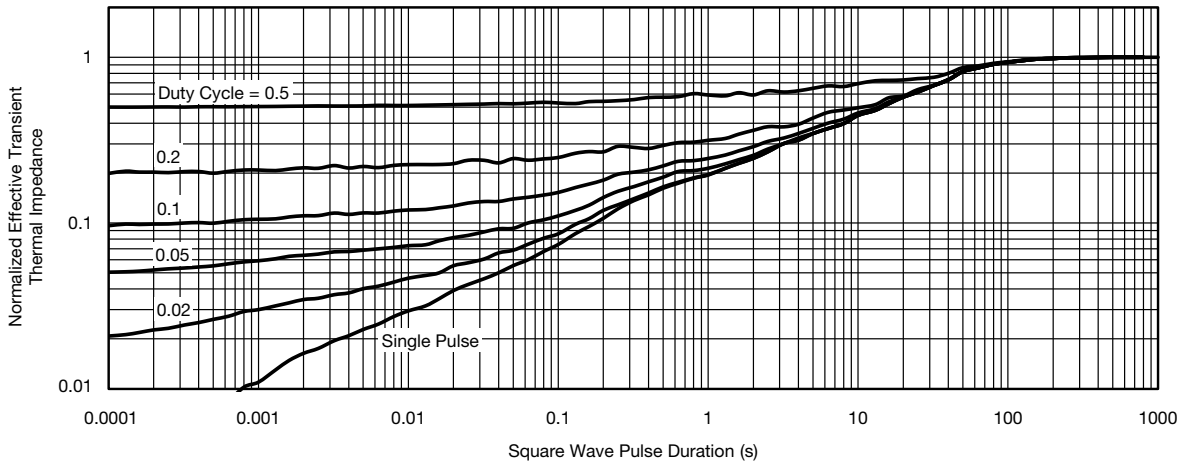


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

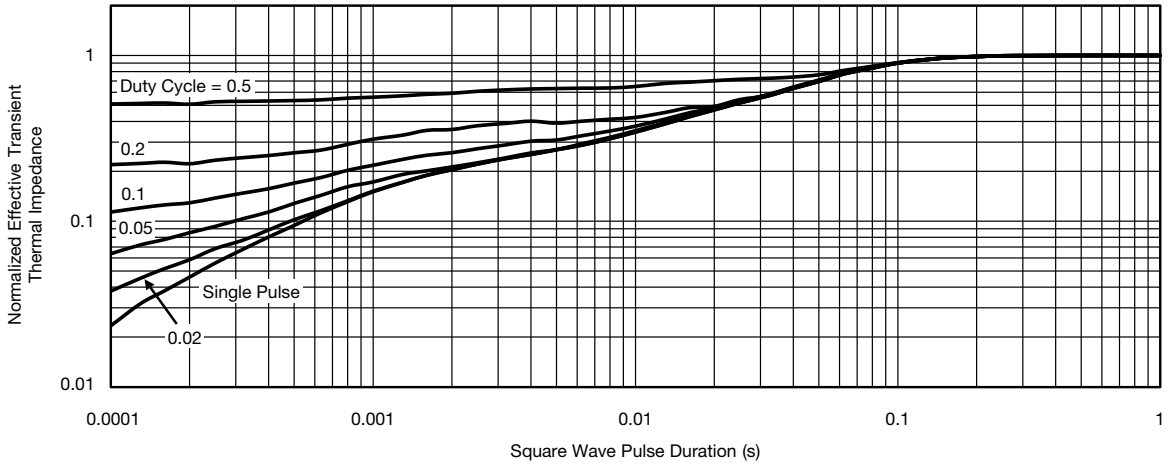


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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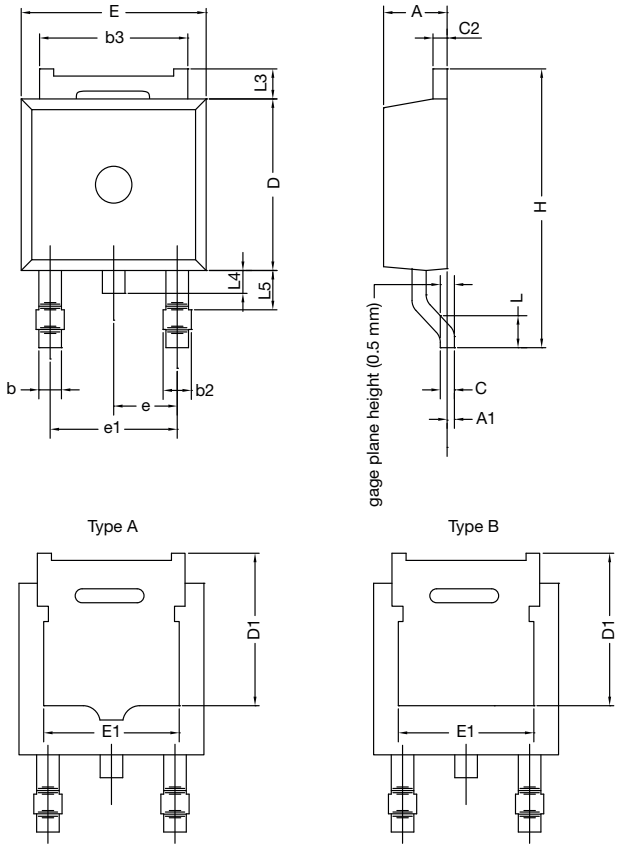
TO-252AA Case Outline

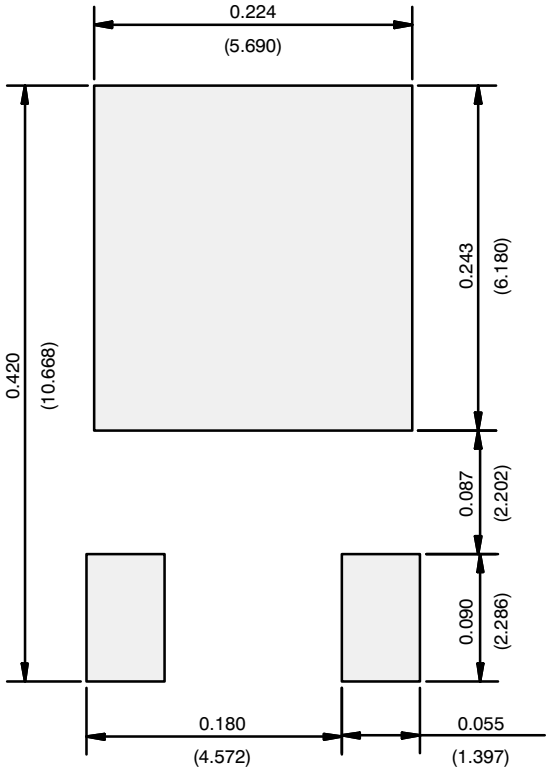


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T25-0122-Rev. C, 12-May-2025 DWG: 6019				

Notes

- Dimension L3 is for reference only
- Dimension D1 and E1 on type A and B is the same

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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